


FS5ASH-06

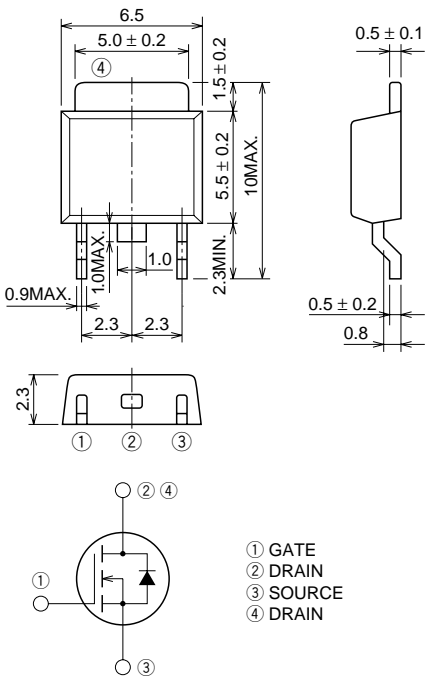
HIGH-SPEED SWITCHING USE

FS5ASH-06



- 2.5V DRIVE
- V_{DSS} 60V
- $r_{DS(ON)}(MAX)$ 0.15Ω
- I_D 5A
- Integrated Fast Recovery Diode (TYP.) 45ns

OUTLINE DRAWING Dimensions in mm



① GATE
② DRAIN
③ SOURCE
④ DRAIN

MP-3

APPLICATION

Motor control, Lamp control, Solenoid control
DC-DC converter, etc.

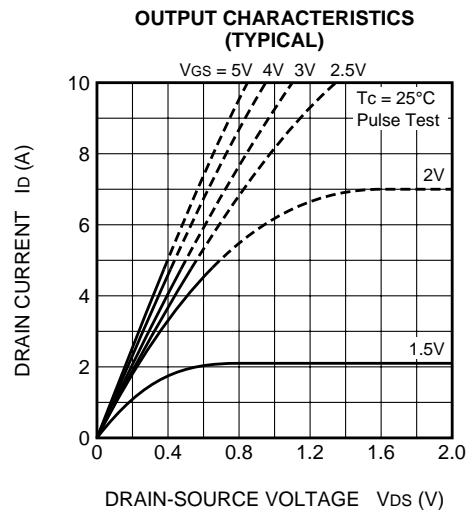
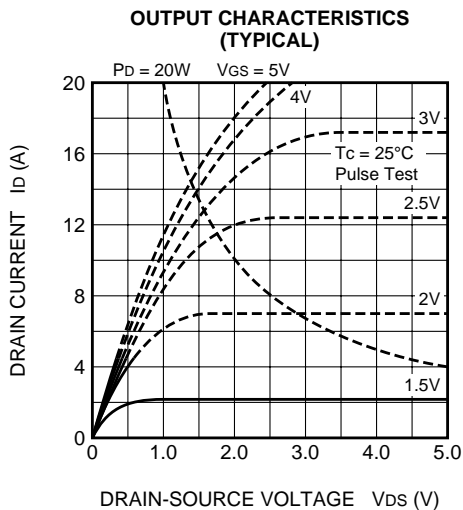
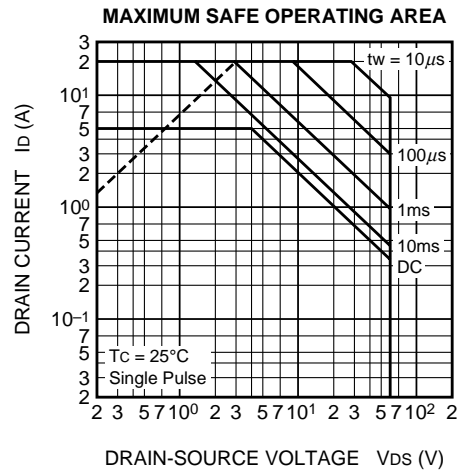
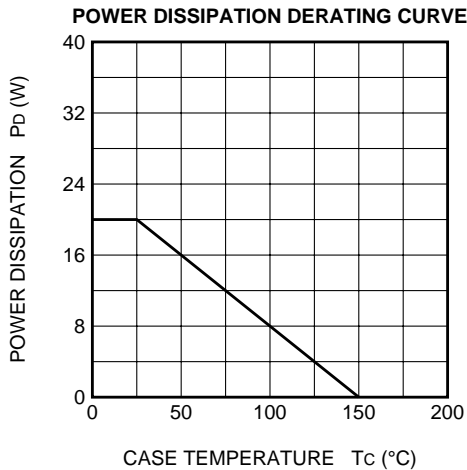
MAXIMUM RATINGS (Tc = 25°C)

Symbol	Parameter	Conditions	Ratings	Unit
V_{DSS}	Drain-source voltage	$V_{GS} = 0V$	60	V
V_{GSS}	Gate-source voltage	$V_{DS} = 0V$	± 10	V
I_D	Drain current		5	A
I_{DM}	Drain current (Pulsed)		20	A
I_{DA}	Avalanche drain current (Pulsed)	$L = 100\mu H$	5	A
I_S	Source current		5	A
I_{SM}	Source current (Pulsed)		20	A
P_D	Maximum power dissipation		20	W
T_{ch}	Channel temperature		-55 ~ +150	°C
T_{stg}	Storage temperature		-55 ~ +150	°C
—	Weight	Typical value	0.26	g

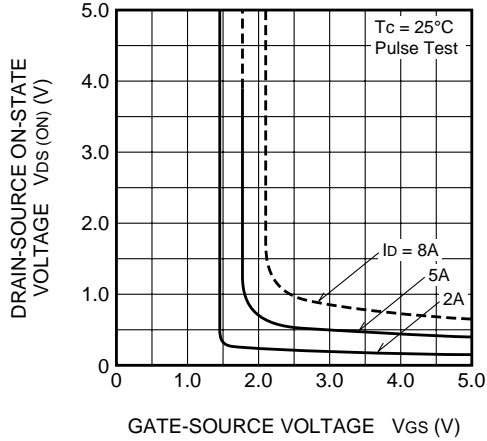
ELECTRICAL CHARACTERISTICS (T_{ch} = 25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V (BR) DSS	Drain-source breakdown voltage	I _D = 1mA, V _{GS} = 0V	60	—	—	V
I _{GSS}	Gate-source leakage current	V _{GS} = ±10V, V _{DS} = 0V	—	—	±0.1	μA
I _{DSS}	Drain-source leakage current	V _{DS} = 60V, V _{GS} = 0V	—	—	0.1	mA
V _{GS} (th)	Gate-source threshold voltage	I _D = 1mA, V _{DS} = 10V	0.6	0.9	1.2	V
r _{DS} (ON)	Drain-source on-state resistance	I _D = 2A, V _{GS} = 4V	—	0.11	0.15	Ω
r _{DS} (ON)	Drain-source on-state resistance	I _D = 2A, V _{GS} = 2.5V	—	0.13	0.20	Ω
V _{DS} (ON)	Drain-source on-state voltage	I _D = 2A, V _{GS} = 4V	—	0.22	0.3	V
y _{fs}	Forward transfer admittance	I _D = 2A, V _{DS} = 5V	—	10	—	S
C _{iss}	Input capacitance	V _{DS} = 10V, V _{GS} = 0V, f = 1MHz	—	540	—	pF
C _{oss}	Output capacitance		—	120	—	pF
C _{rss}	Reverse transfer capacitance		—	40	—	pF
t _d (on)	Turn-on delay time	V _{DD} = 30V, I _D = 2A, V _{GS} = 4V, R _{GEN} = R _{GS} = 50Ω	—	12	—	ns
t _r	Rise time		—	20	—	ns
t _d (off)	Turn-off delay time		—	50	—	ns
t _f	Fall time		—	32	—	ns
V _{SD}	Source-drain voltage	I _S = 2A, V _{GS} = 0V	—	1.0	1.5	V
R _{th} (ch-c)	Thermal resistance	Channel to case	—	—	6.25	°C/W
t _{rr}	Reverse recovery time	I _S = 5A, di _s /dt = -100A/μs	—	45	—	ns

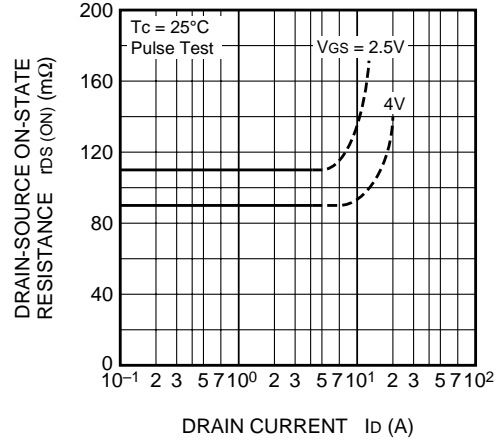
PERFORMANCE CURVES



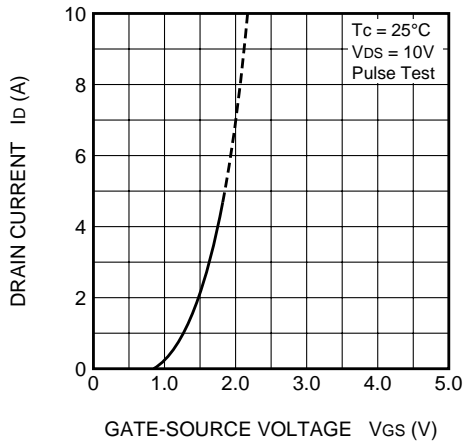
ON-STATE VOLTAGE VS. GATE-SOURCE VOLTAGE (TYPICAL)



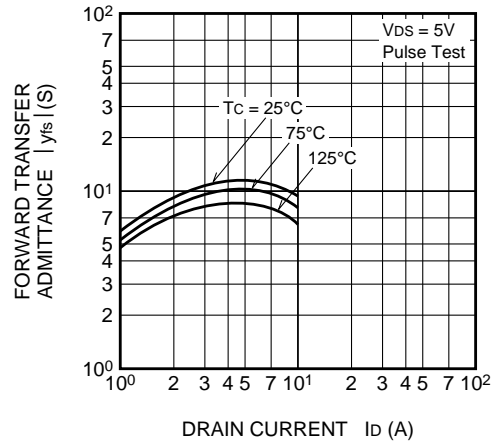
ON-STATE RESISTANCE VS. DRAIN CURRENT (TYPICAL)



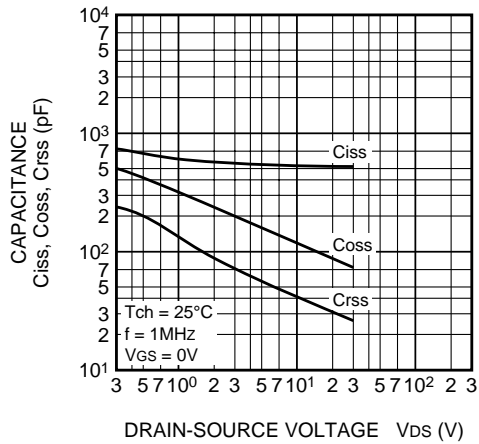
TRANSFER CHARACTERISTICS (TYPICAL)



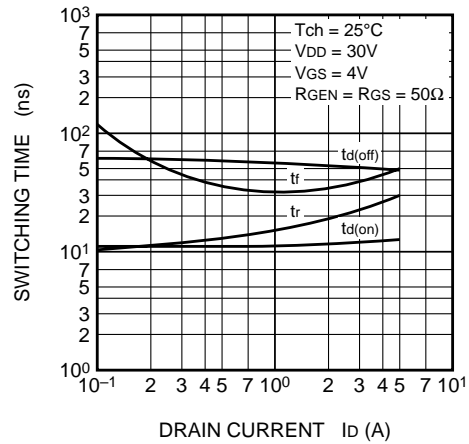
FORWARD TRANSFER ADMITTANCE VS. DRAIN CURRENT (TYPICAL)



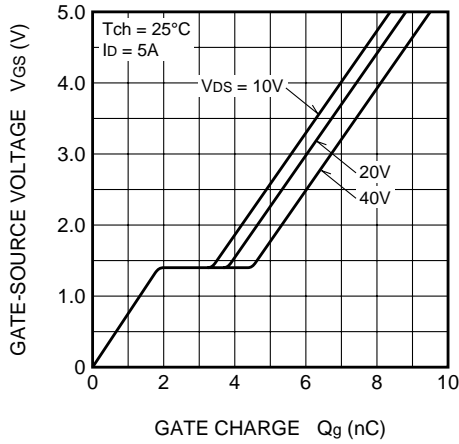
CAPACITANCE VS. DRAIN-SOURCE VOLTAGE (TYPICAL)



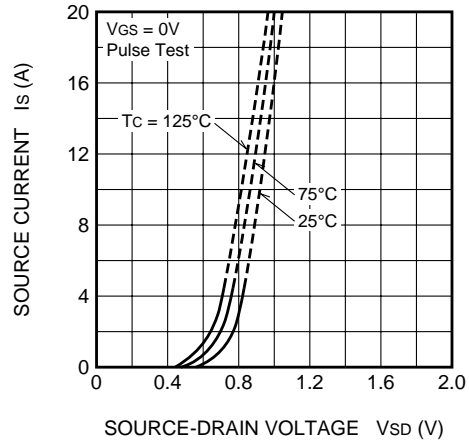
SWITCHING CHARACTERISTICS (TYPICAL)



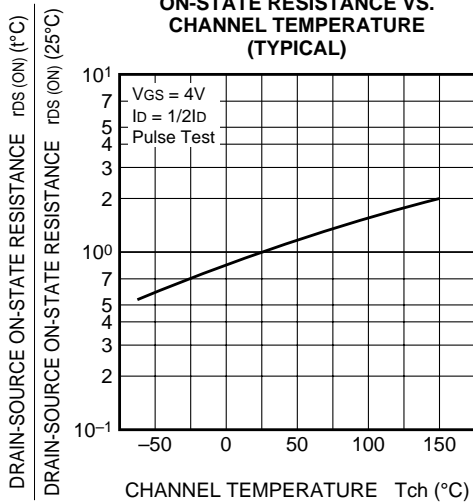
GATE-SOURCE VOLTAGE VS. GATE CHARGE (TYPICAL)



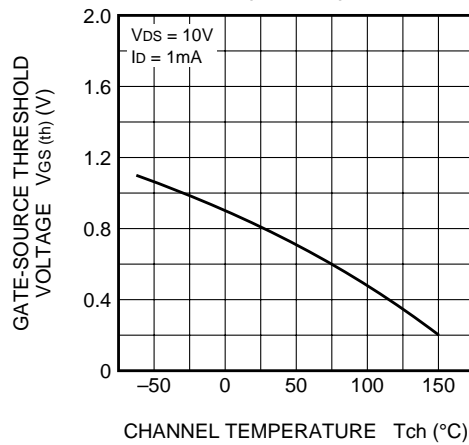
SOURCE-DRAIN DIODE FORWARD CHARACTERISTICS (TYPICAL)



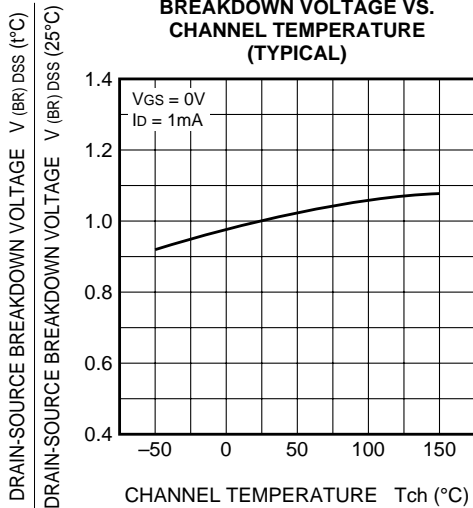
ON-STATE RESISTANCE VS. CHANNEL TEMPERATURE (TYPICAL)



THRESHOLD VOLTAGE VS. CHANNEL TEMPERATURE (TYPICAL)



BREAKDOWN VOLTAGE VS. CHANNEL TEMPERATURE (TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS

